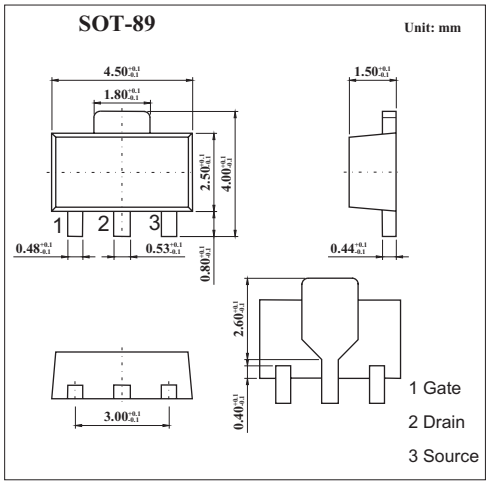
TY Semicondutor®

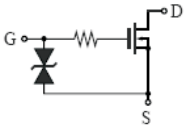
Product specification

2SK2211



■ Features

- Low ON-resistance $R_{DS(ON)}$
- High-speed switching



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Drain to source voltage	V_{DSS}	30	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	±1.0	A
	I_{dp} *	±2.0	A
Power dissipation	P_D	1	W
Channel temperature	T_{ch}	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

* PW≤10ms,Duty Cycle≤50%

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain to source breakdown voltage	V_{DSS}	I_D=0.1mA,V_{GS}=0	30			V
Gate to source voltage	V_{GSS}	I_{GS}=0.1mA,V_{GS}=0	±20			V
Drain cut-off current	I_{DSS}	V_{DS}=25V,V_{GS}=0			1.0	μA
Gate leakage current	I_{GSS}	V_{GS}=±15V,V_{DS}=0			±10	μA
Gate threshold voltage	V_{th}	V_{DS}=5V,I_D=1mA	0.8		2	V
Forward transfer admittance	$\|Y_{fs}\|$	V_{DS}=10V,I_D=0.5A	0.5			S
Drain to source on-state resistance	$R_{DS(on)}$	V_{GS}=4V,I_D=0.5A		0.48	0.75	Ω
		V_{GS}=10V,I_D=0.5A		0.35	0.6	Ω
Input capacitance	C_{iss}	V_{DS}=10V,V_{GS}=0,f=1MHZ		87		pF
Output capacitance	C_{oss}			69		pF
Reverse transfer capacitance	C_{rss}			23		pF
Turn-on delay time	t_{on}	I_D=0.5A,$V_{GS(on)}$=10V,R_L=10Ω,V_{DD}=10V		12		ns
Rise time	t_r			160		ns
Turn-off delay time	t_{off}			60		ns

■ Marking

Marking	2M